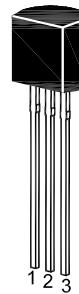


BC546...BC550

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier application

These transistors are subdivided into three groups A, B and C according to their current gain.



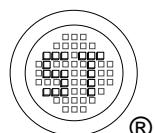
1. Collector 2. Base 3. Emitter
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage BC546 BC547, BC550 BC548, BC549	V_{CBO}	80	V
		50	
		30	
Collector Emitter Voltage BC546 BC547, BC550 BC548, BC549	V_{CEO}	65	V
		45	
		30	
Emitter Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$	h_{FE}	110	220	-
		200	450	-
		420	800	-
Collector Base Cutoff Current at $V_{CB} = 30 \text{ V}$	I_{CBO}	-	15	nA
Emitter Base Cutoff Current at $V_{EB} = 5 \text{ V}$	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100 \mu\text{A}$ BC546 BC547, BC550 BC548, BC549	$V_{(BR)CBO}$	80	-	V
		50	-	
		30	-	
Collector Emitter Breakdown Voltage at $I_C = 1 \text{ mA}$ BC546 BC547, BC550 BC548, BC549	$V_{(BR)CEO}$	65	-	V
		45	-	
		30	-	
Emitter Base Breakdown Voltage at $I_E = 10 \mu\text{A}$	$V_{(BR)EBO}$	6	-	V



BC546...BC550

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Collector Emitter Saturation Voltage at $I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$ at $I_C = 100 \text{ mA}$, $I_B = 5 \text{ mA}$	$V_{CE(\text{sat})}$	-	0.25 0.6	V
Base Emitter On Voltage at $V_{CE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$ at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$	$V_{BE(\text{on})}$	0.55 -	0.7 0.77	V
Transition Frequency at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	100	-	MHz
Collector Base Capacitance at $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{cb}	-	6	pF

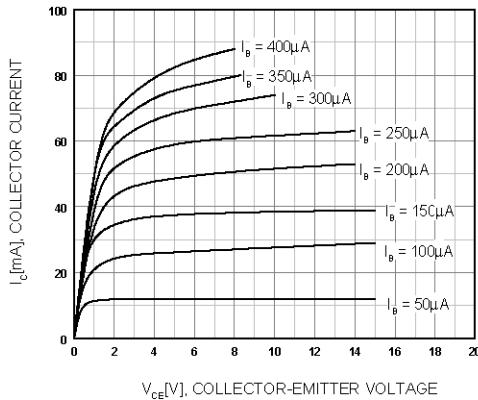


Figure 1. Static Characteristic

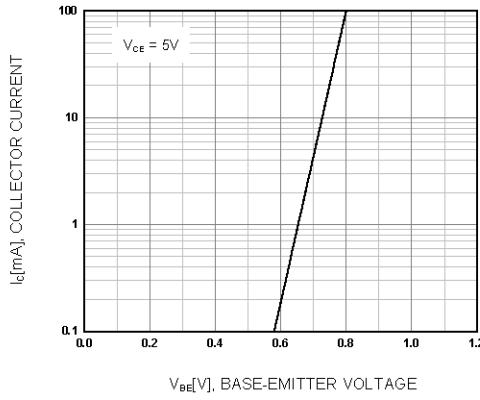


Figure 2. Transfer Characteristic

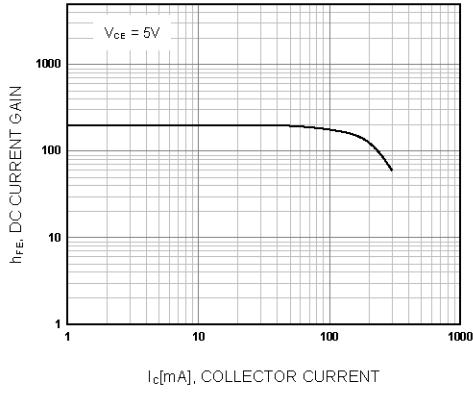


Figure 3. DC current Gain

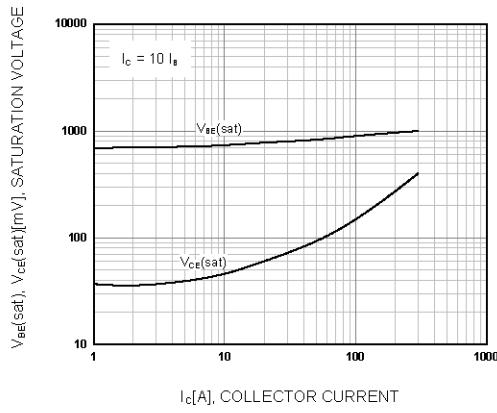


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

